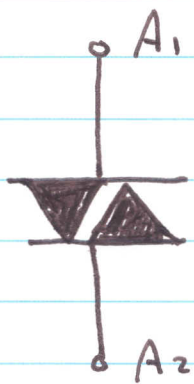
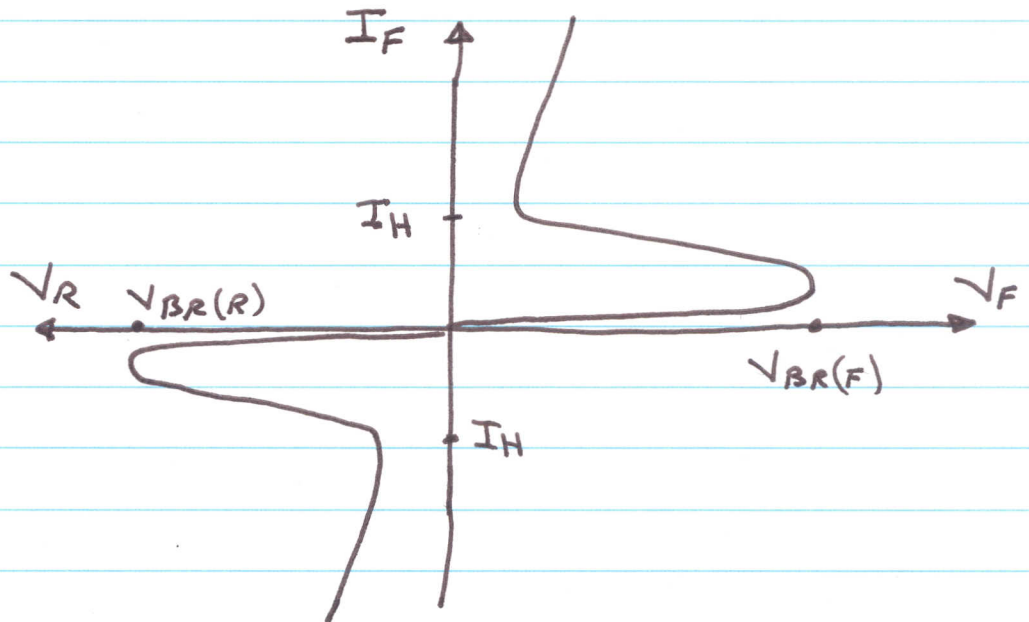


# The Diac

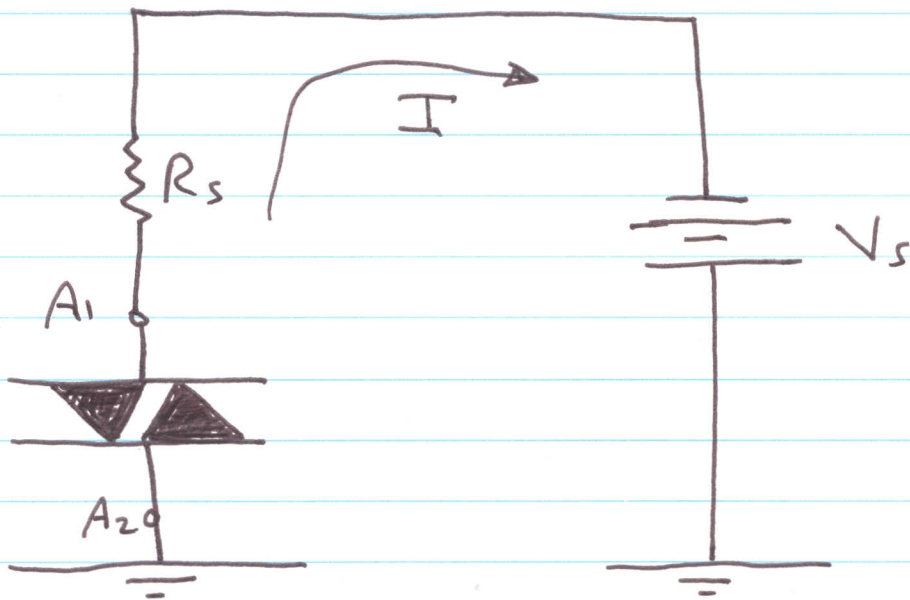
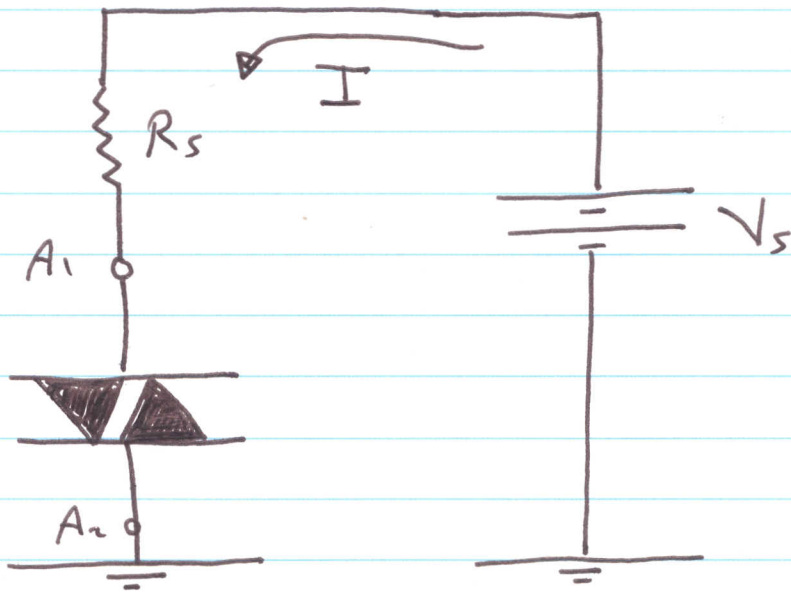


Circuit Symbol

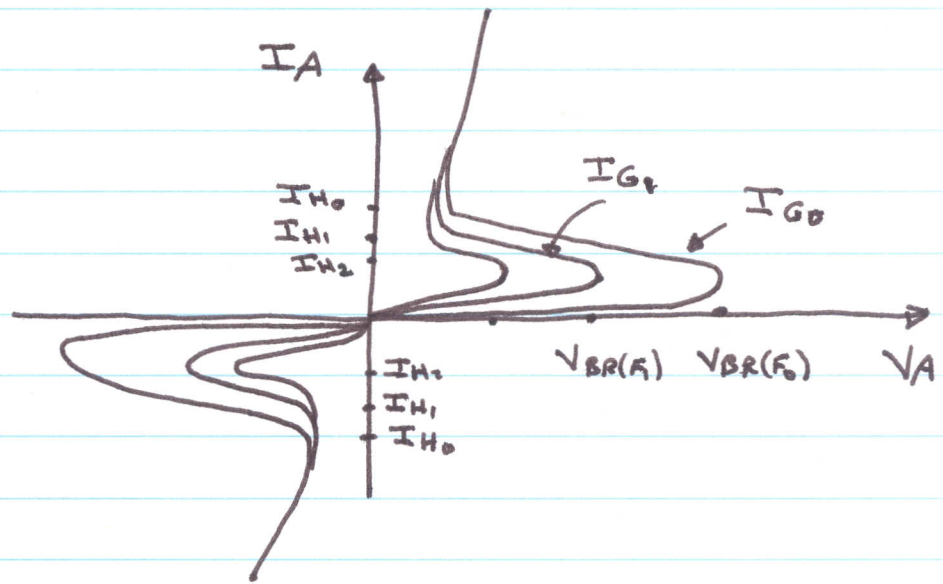
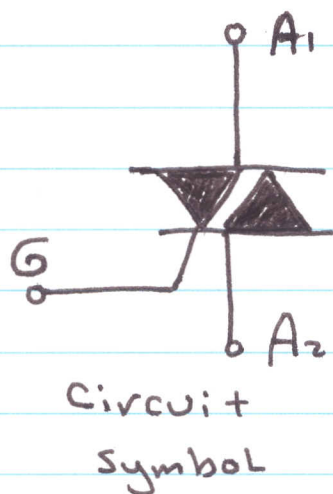


Characteristic Curve

- It is a two terminal device
- It can conduct current in either direction when properly activated
- Conduction occurs when the breakover voltage is reached with either polarity
- The device turns off when the current drops below the holding value ( $I_H$ )
- The device functions like two parallel Shockley diodes turned in opposite direction



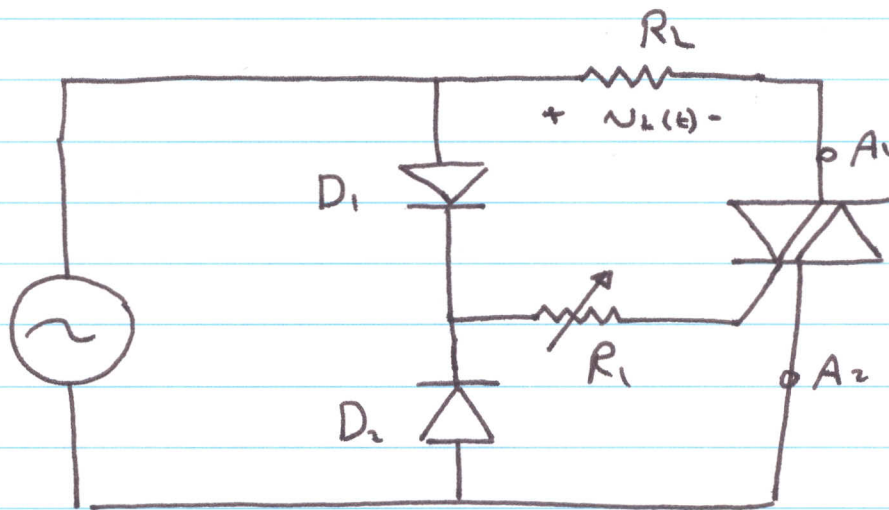
# The Triac



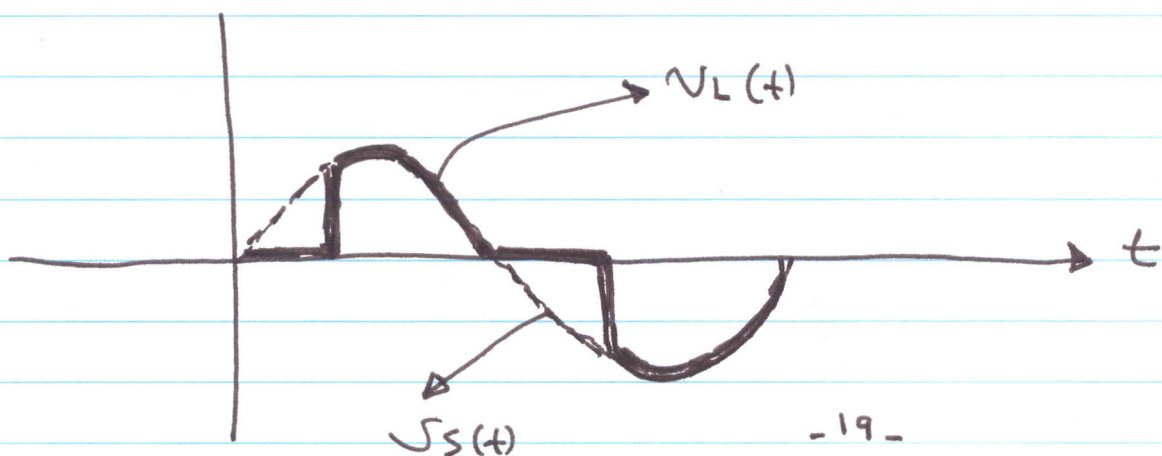
characteristic Curves

- A triac is like a diac with a gate
- The triac functions like two SCR connected in parallel and in opposite direction with a common gate terminal.
- The triac can conduct current in either direction when it is triggered on, depending on the polarity of the voltage across its  $A_1$  and  $A_2$  terminals.
- The triac turns off when the current drops below the holding value ( $I_H$ ).

# Triac Application

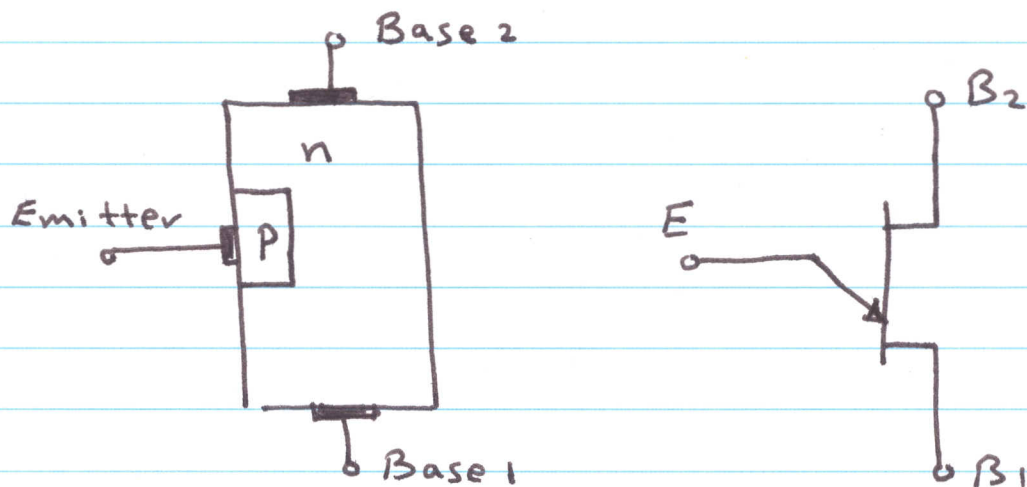


- Diode  $D_1$  Conducts during the positive half-cycle
- The value of  $R_1$  sets the point on the positive half cycle at which the triac triggers
- Diode  $D_2$  Conducts during the negative half cycle
- The value of  $R_1$  sets the trigger point



# The Unijunction Transistor : UJT

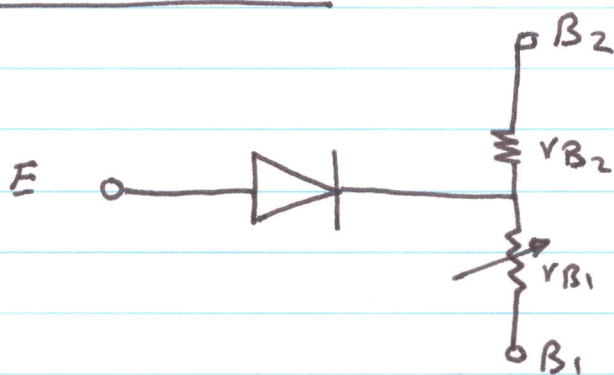
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- UJT is a three terminal device ; E, B<sub>1</sub>, and B<sub>2</sub>
- UJT has one pn junction

## Equivalent Circuit

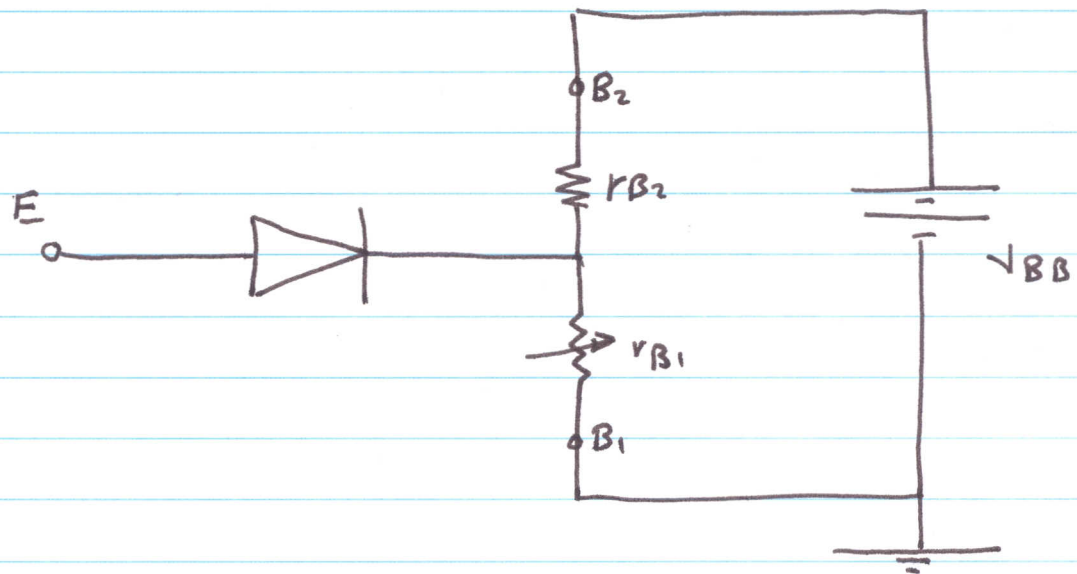
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$r_{B1}$ ,  $r_{B2}$  are the dynamic resistance

$$r_{BB} = r_{B1} + r_{B2} \quad \text{interbase resistance}$$

$r_{B1}$  varies inversely with emitter current



To find the UJT

$$V_{EB1} \gg V_D + \frac{r_{B1}}{r_{B1} + r_{B2}} V_{BB} = V_p$$

$$V_{EB1} \gg V_D + \frac{r_{B1}}{r_{BB}} V_{BB} = V_p$$

$$V_{EB1} \gg V_D + \eta V_{BB} = V_p$$

$$\eta = \frac{r_{B1}}{r_{BB}} \equiv \text{standoff ratio}$$

$V_p \equiv$  peak point voltage

As long as the applied emitter voltage  $V_{EB1}$

is less than  $V_p$ ; there is no emitter

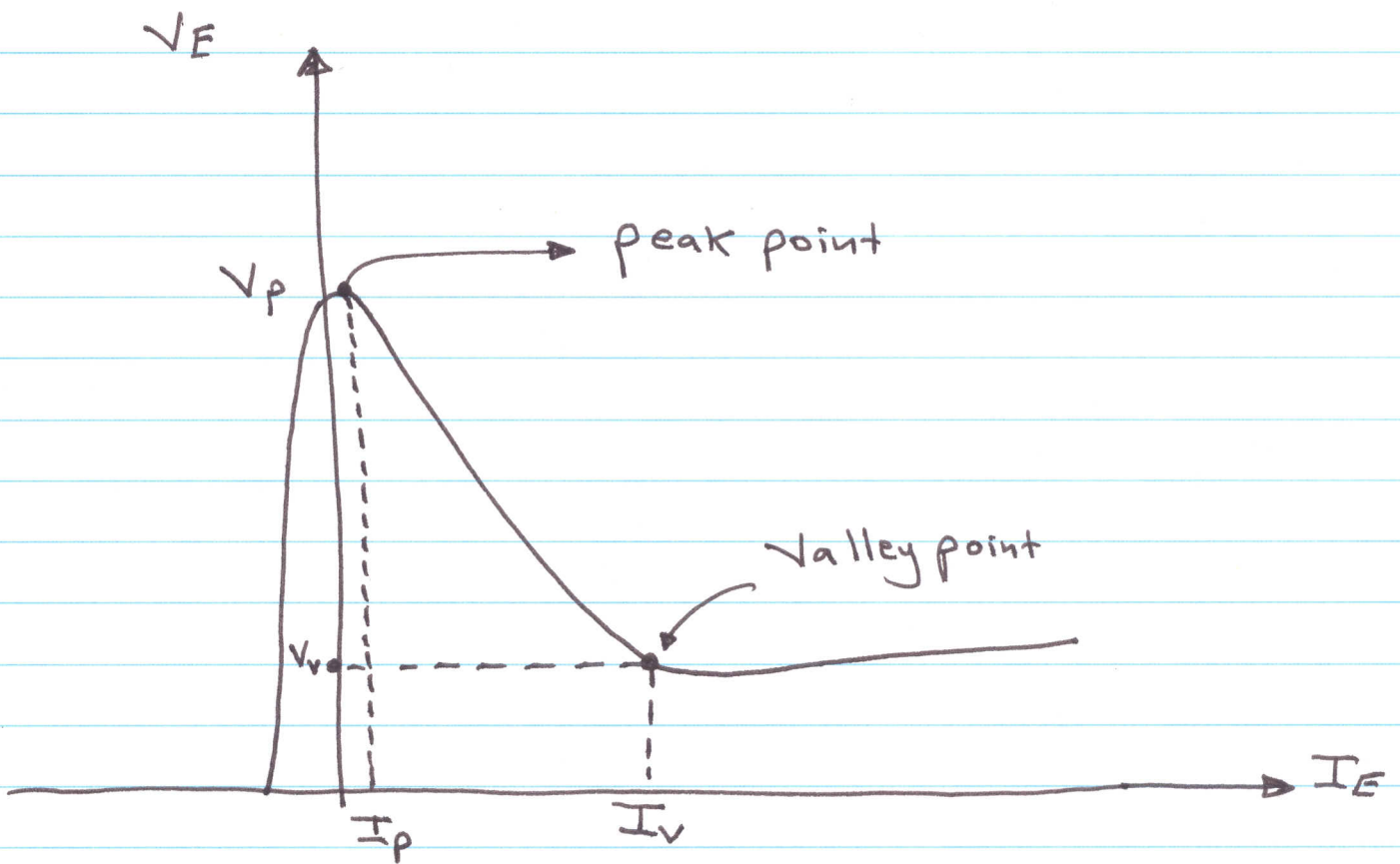
current because the pn junction is not

forward biased

- When  $V_{EB}$  reaches  $V_p$ , the pn junction becomes forward biased and  $I_E$  begins.
- Holes are injected into the n-type bar from the p-type emitter
- $r_{B1}$  decreases
- After turn on, the UJT operates in a negative resistance region up to a certain value of  $I_E$ .
- After the peak point ( $V_E = V_p$  and  $I_E = I_p$ )  $V_E$  decreases as  $I_E$  continues to increase, thus producing the negative resistance characteristic.
- Beyond the valley point ( $V_E = V_v$  and  $I_E = I_v$ ) , the device is in saturation

# UJT Characteristic Curve

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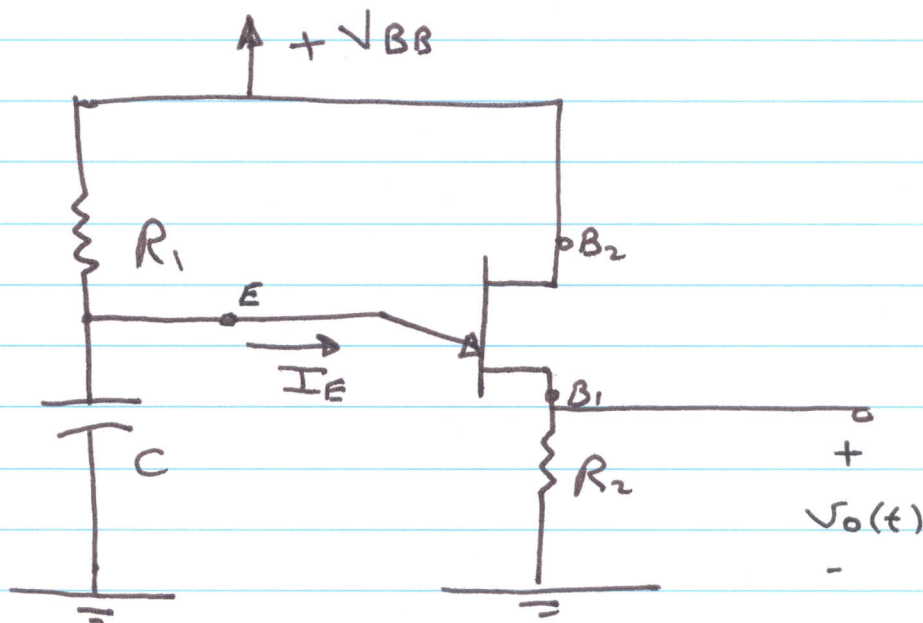
$V_v \equiv$  Valley Voltage

$I_v \equiv$  Valley Current



# A UJT Application

## Relaxation Oscillator



- When the dc power supply is applied, the capacitor C charges through  $R_1$  until it reaches  $V_p$
- At this point, the pn junction becomes forward biased and  $I_E$  conducts, and  $V_{B_1}$  decreases
- The capacitor then quickly discharges through  $R_2$  and  $V_{B_1}$
- When the capacitor voltage decreases to the valley voltage, the UJT turns OFF

- The Capacitor begins to charge again and the cycle is repeated.

